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Innovative Silicon's Dr. Pierre Fazan Invited to Present at SSDM in Japan

Memory luminary to give overview of capacitor-less DRAM technologies and their challenges

SANTA CLARA, Calif. — September 22, 2009 — Innovative Silicon, Inc. (ISi), developer of the Z-RAM® zero-capacitor, floating body (FB) memory technology, today announced that its founder and CTO, Dr. Pierre Fazan will be delivering a presentation titled “Overview and Future Challenges of Capacitor-less DRAM Technologies for High Density Memory Applications” at [SSMD2009](#). Dr. Fazan will be speaking in the advanced memory core area, along with speakers from IMEC, Panasonic and Toshiba.

Event Logistics:

Date: Wednesday, October 7, 2009
Time/Specifics: 1:30 p.m., Area 4, Session 6-1-1
Location: Sendai Kokusai Hotel, Sendai, Japan

About Dr. Fazan's Presentation

Dr. Fazan has long proposed that scaling 1 transistor/1 capacitor DRAM bit cells below the 50nm node dimension represents a serious challenge as contacts, device aspect ratios and capacitor materials are approaching manufacturing limits. The capacitor-less RAM cell is one of the leading contenders to address scaling and performance limitations as it uses only conventional materials and is therefore fully compatible with CMOS processes. Following the introduction of a technology exploiting a bipolar junction transistor (BJT) operation, capacitor-less RAM cells are now well suited to replace standalone DRAM cells in sub 50nm memories.

About SSDM2009

The 2009 International Conference on Solid State Devices and Materials (SSDM2009) is one of the most important and prestigious international conferences held in Japan. SSDM has provided an excellent opportunity to present and discuss key aspects of solid state devices and materials since its inception

in 1969. Since 1999, program sub-committees have been established to further advance the SSDM conference activity. This organizational change has led to higher quality paper selection, resulting in a higher level of presentations and discussions in various potential subject areas. The conference has 10 sub-committees in core areas and 4 sub-committees in strategic areas, which are continuously focused on pointing out future directions in solid state devices and materials research. For more information see <http://www.ssdm.jp/>.

About Innovative Silicon

Innovative Silicon, Inc. (ISi) licenses its ultra-dense Z-RAM® floating body memory technology to stand-alone DRAM manufacturers so they may manufacture the lowest-cost, most-advanced memory ICs. Licensees include Hynix Semiconductor for use in advanced DRAM chips. The heart of the Z-RAM floating body technology is the “zero-capacitor,” single-transistor bit cell that eliminates the complex capacitor found in today’s DRAM technologies – making it the world’s lowest-cost and most-scalable memory technology. Since 2003, the company has closed \$47 million in venture capital funding, received numerous industry awards such as *IEEE Spectrum Magazine*’s “2007 Emerging Technology Most Likely to Succeed,” been granted dozens of patents, and established R&D, engineering and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

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